

GENERAL DESCRIPTION

The EM6112K800V is a 4,194,304-bit low power CMOS static random access memory organized as 524,288 words by 8 bits. It is fabricated using very high performance, high reliability CMOS technology. Its standby current is stable within the range of operating temperature.

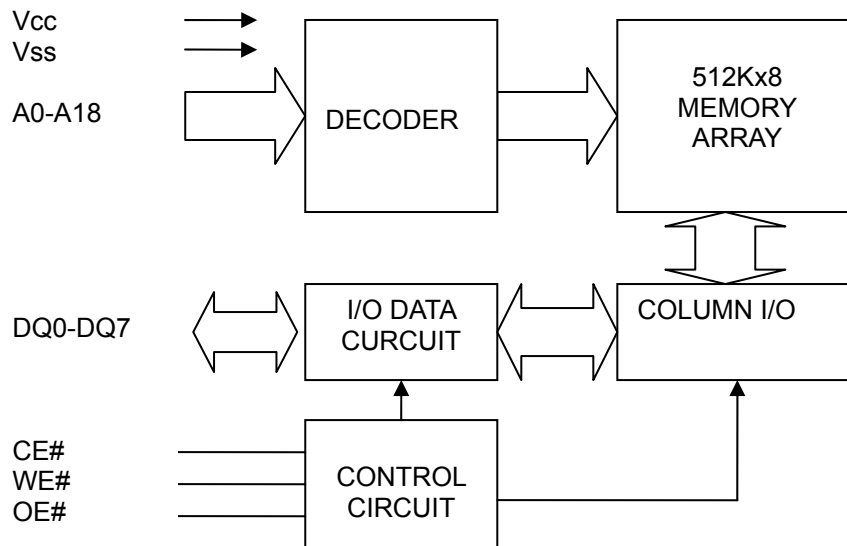
The EM6112K800V is well designed for low power application, and particularly well suited for battery back-up nonvolatile memory application.

The EM6112K800V operates from a single power supply of 2.7V ~ 3.6V and all inputs and outputs are fully TTL compatible

FEATURES

- Fast access time: 45/55/70ns
- Low power consumption:
Operating current: 40/30/20mA (TYP.)
Standby current: -L/-LL version 20/2µA (TYP.)
- Single 2.7V ~ 3.6V power supply
- All inputs and outputs TTL compatible
- Fully static operation
- Tri-state output
- Data retention voltage: 1.5V (MIN.)
- Package:
32-pin 450 mil SOP
32-pin 8mm x 20mm TSOP-I
32-pin 8mm x 13.4mm STSOP
36-ball 6mm x 8mm TFBGA

FUNCTIONAL BLOCK DIAGRAM

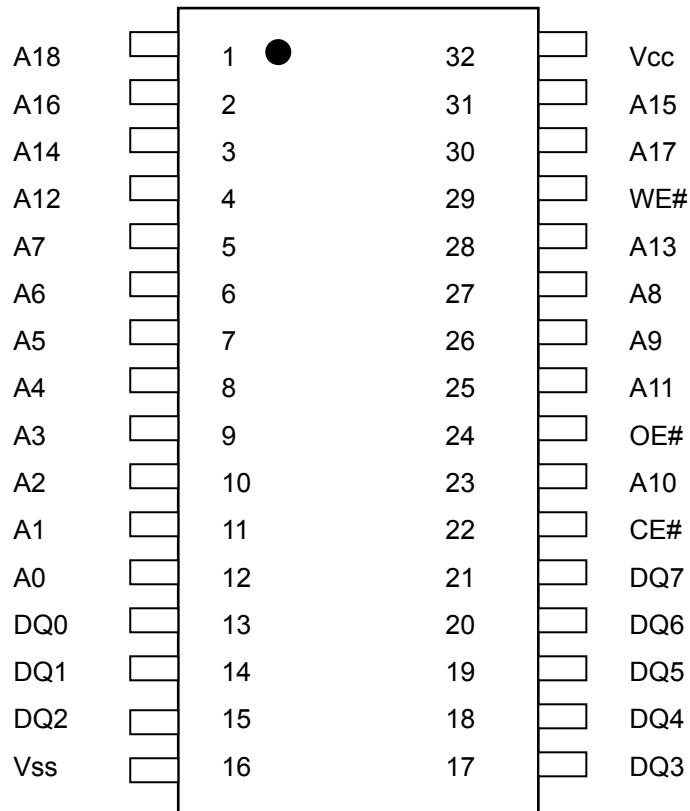


PIN DESCRIPTION

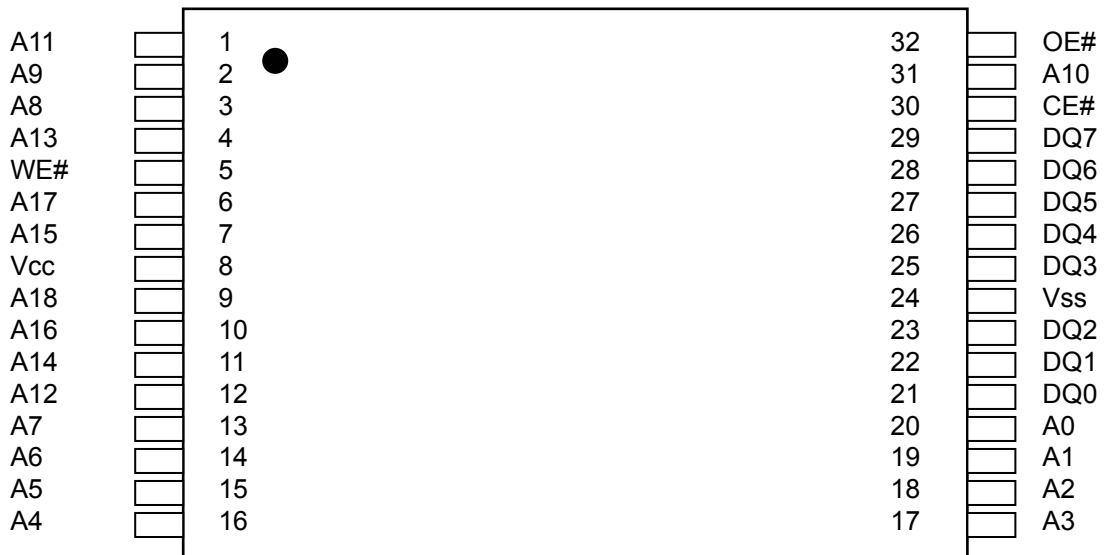
SYMBOL	DESCRIPTION
A0 - A18	Address Inputs
DQ0 – DQ7	Data Inputs/Outputs
CE#	Enable Input
WE#	Write Enable Input
OE#	Output Enable Input
Vcc	Power Supply
Vss	Ground

PIN CONFIGURATION

SOP



TSOP-I/STSOP



TFBGA

A	A0	A1	NC	A3	A6	A8
B	DQ4	A2	WE#	A4	A7	DQ0
C	DQ5		NC	A5		DQ1
D	Vss					Vcc
E	Vcc					Vss
F	DQ6		A17	A18		DQ2
G	DQ7	OE#	CE#	A16	A15	DQ3
H	A9	A10	A11	A12	A13	A14
	1	2	3	4	5	6

ABSOLUTE MAXIMUM RATINGS*

PARAMETER	SYMBOL	RATING	UNIT
Terminal Voltage with Respect to V _{SS}	V _{TERM}	-0.5 to 4.6	V
Operating Temperature	T _A	0 to 70(C grade)	°C
		-20 to 80(E grade)	
		-40 to 85(I grade)	
Storage Temperature	T _{STG}	-65 to 150	°C
Power Dissipation	P _D	1	W
DC Output Current	I _{OUT}	50	mA
Soldering Temperature (under 10 sec)	T _{SOLDER}	260	°C

*Stresses greater than those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to the absolute maximum rating conditions for extended period may affect device reliability.

TRUTH TABLE

MODE	CE#	OE#	WE#	I/O OPERATION	SUPPLY CURRENT
Standby	H	X	X	High-Z	I _{SB} , I _{SB1}
Output Disable	L	H	H	High-Z	I _{CC} , I _{CC1}
Read	L	L	H	D _{OUT}	I _{CC} , I _{CC1}
Write	L	X	L	D _{IN}	I _{CC} , I _{CC1}

Note: H = V_{IH}, L = V_{IL}, X = Don't care.

DC ELECTRICAL CHARACTERISTICS

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP. *5	MAX.	UNIT	
Supply Voltage	V _{CC}		2.7	3.0	3.6	V	
Input High Voltage	V _{IH} *1		2.0	-	V _{CC} +0.3	V	
Input Low Voltage	V _{IL} *2		-0.2	-	0.6	V	
Input Leakage Current	I _{LI}	V _{CC} ≥ V _{IN} ≥ V _{SS}	-1	-	+1	μA	
Output Leakage Current	I _{LO}	V _{CC} ≥ V _{OUT} ≥ V _{SS} , Output Disabled	-1	-	1	μA	
Output High Voltage	V _{OH}	I _{OH} = -1mA	2.2	2.7	-	V	
Output Low Voltage	V _{OL}	I _{OL} = 2mA	-	-	0.4	V	
Average Operating Power supply Current	I _{CC}	Cycle time = Min. CE# = V _{IL} , I _{I/O} = 0mA	-45	-	40	50	mA
			-55	-	30	40	mA
			-70	-	20	30	mA
	I _{CC1}	Cycle time = 1μs CE# ≤ 0.2V and I _{I/O} = 0mA other pins at 0.2V or V _{CC} -0.2V	-	4	5	mA	
Standby Power Supply Current	I _{SB}	CE# = V _{IH}	-	0.3	0.5	mA	
	I _{SB1}	CE# V ≥ V _{CC} - 0.2V	-L	-	20	80	μA
			-LL	-	2	15	μA

Notes:

1. V_{IH}(max) = V_{CC} + 3.0V for pulse width less than 10ns.
2. V_{IL}(min) = V_{SS} - 3.0V for pulse width less than 10ns.
3. Over/Undershoot specifications are characterized, not 100% tested.
4. 10μA for special request
5. Typical values are included for reference only and are not guaranteed or tested.
Typical values are measured at V_{CC} = V_{CC}(TYP.) and T_A = 25°C

CAPACITANCE ($T_A = 25^\circ\text{C}$, $f = 1.0\text{MHz}$)

PARAMETER	SYMBOL	MIN.	MAX.	UNIT
Input Capacitance	C_{IN}	-	6	pF
Input/Output Capacitance	$C_{I/O}$	-	8	pF

Note : These parameters are guaranteed by device characterization, but not production tested.

AC TEST CONDITIONS

Input Pulse Levels	0.2V to $V_{CC} - 0.2\text{V}$
Input Rise and Fall Times	3ns
Input and Output Timing Reference Levels	1.5V
Output Load	$C_L = 30\text{pF} + 1\text{TTL}$, $I_{OH}/I_{OL} = -1\text{mA}/2\text{mA}$

AC ELECTRICAL CHARACTERISTICS**READ CYCLE**

PARAMETER	SYM.	-45		-55		70		UNIT
		MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Read Cycle Time	t_{RC}	45	-	55	-	70	-	ns
Address Access Time	t_{AA}	-	45	-	55	-	70	ns
Chip Enable Access Time	t_{ACE}	-	45	-	55	-	70	ns
Output Enable Access Time	t_{OE}	-	25	-	30	-	35	ns
Chip Enable to Output in Low-Z	t_{CLZ}^*	10	-	10	-	10	-	ns
Output Enable to Output in Low-Z	t_{OLZ}^*	5	-	5	-	5	-	ns
Chip Disable to Output in High-Z	t_{CHZ}^*	-	15	-	20	-	25	ns
Output Disable to Output in High-Z	t_{OHZ}^*	-	15	-	20	-	25	ns
Output Hold from Address Change	t_{OH}	10	-	10	-	10	-	ns

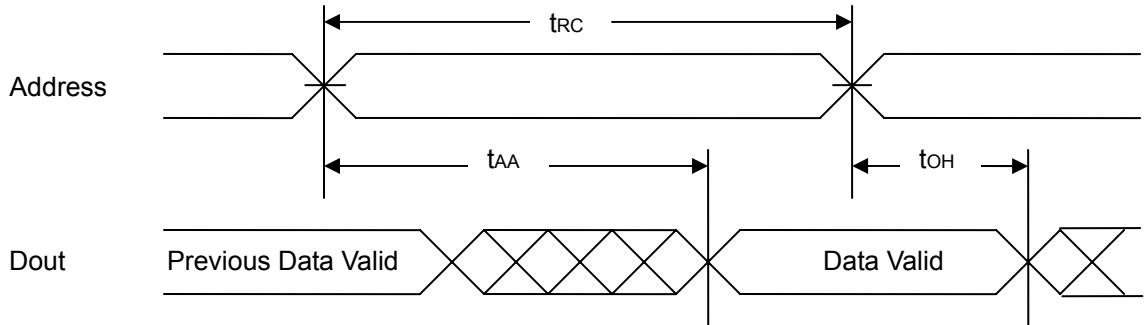
WRITE CYCLE

PARAMETER	SYM.	-45		-55		70		UNIT
		MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Write Cycle Time	t_{WC}	45	-	55	-	70	-	ns
Address Valid to End of Write	t_{AW}	40	-	50	-	60	-	ns
Chip Enable to End of Write	t_{CW}	40	-	50	-	60	-	ns
Address Set-up Time	t_{AS}	0	-	0	-	0	-	ns
Write Pulse Width	t_{WP}	35	-	45	-	55	-	ns
Write Recovery Time	t_{WR}	0	-	0	-	0	-	ns
Data to Write Time Overlap	t_{DW}	20	-	25	-	30	-	ns
Data Hold from End of Write Time	t_{DH}	0	-	0	-	0	-	ns
Output Active from End of Write	t_{OW}^*	5	-	5	-	5	-	ns
Write to Output in High-Z	t_{WHZ}^*	-	15	-	20	-	25	ns

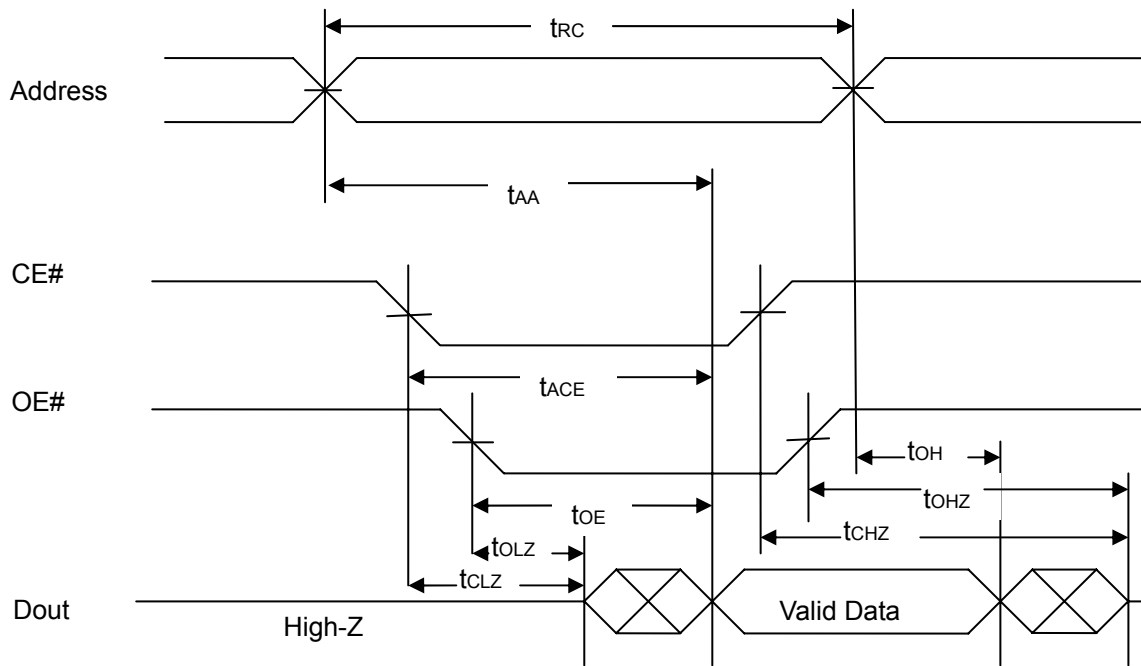
*These parameters are guaranteed by device characterization, but not production tested.

TIMING WAVEFORMS

READ CYCLE 1 (Address Controlled) (1,2)



READ CYCLE 2 (CE#, CE2 and OE# controlled) (1,3,4,5)



Notes :

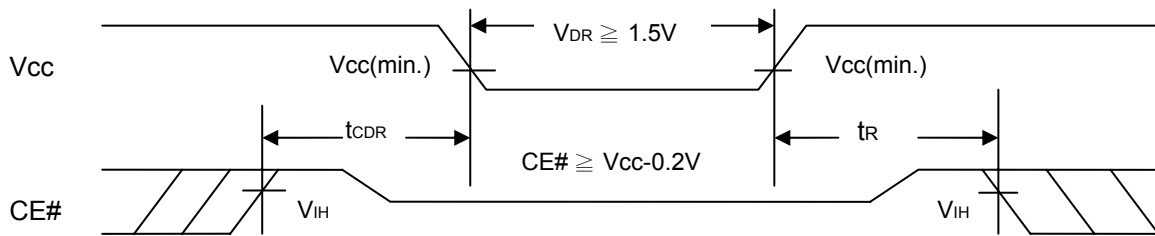
1. WE# is high for read cycle.
2. Device is continuously selected OE# = low, CE# = low.
3. Address must be valid prior to or coincident with CE# = low; otherwise t_{AA} is the limiting parameter.
4. t_{CLZ} , t_{OLZ} , t_{CHZ} and t_{OHZ} are specified with $C_L = 5\text{pF}$. Transition is measured $\pm 500\text{mV}$ from steady state.
5. At any given temperature and voltage condition, t_{CHZ} is less than t_{CLZ} , t_{OHZ} is less than t_{OLZ} .

DATA RETENTION CHARACTERISTICS

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT	
V _{CC} for Data Retention	V _{DR}	CE# V ≥ V _{CC} - 0.2V	1.5	-	3.6	V	
Data Retention Current	I _{DR}	V _{CC} = 1.5V CE# V ≥ V _{CC} - 0.2V	-L	-	1	50	μA
			-LL	-	0.5	8	μA
			-LLE		0.5	12	μA
			-LLI				
Chip Disable to Data Retention Time	t _{CDR}	See Data Retention Waveforms (below)	0	-	-	ns	
Recovery Time	t _R		t _{RC} *	-	-	ns	

t_{RC}* = Read Cycle Time

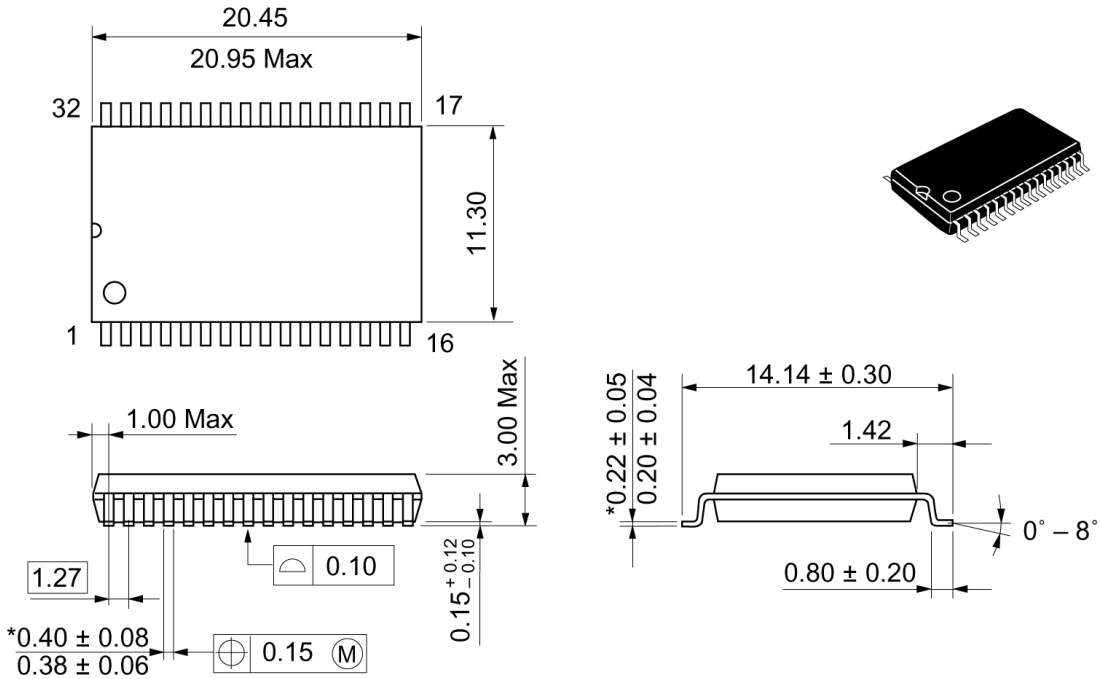
DATA RETENTION WAVEFORM



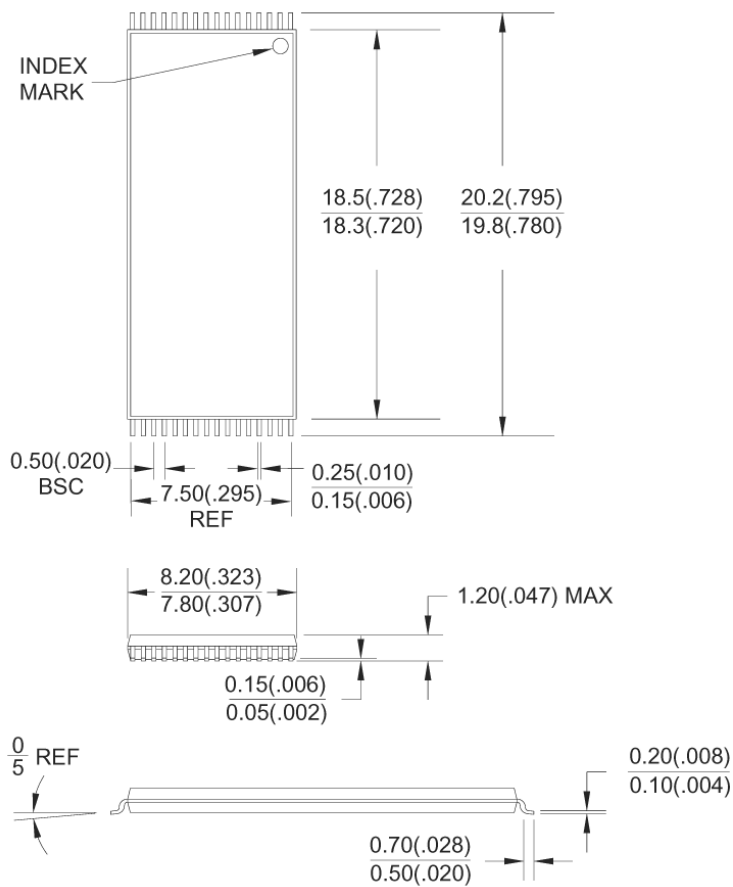
PACKAGE OUTLINE DIMENSION

32 pin 450 mil SOP Package Outline Dimension

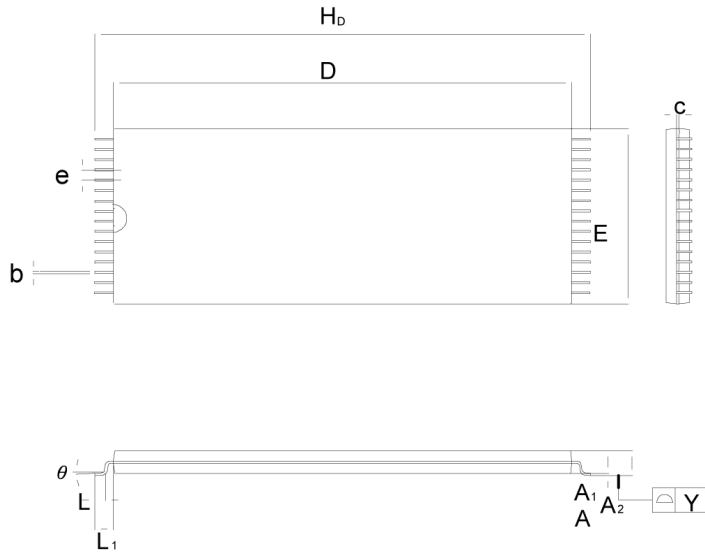
Unit: mm



32 pin 8mm x 20mm TSOP-I Package Outline Dimension

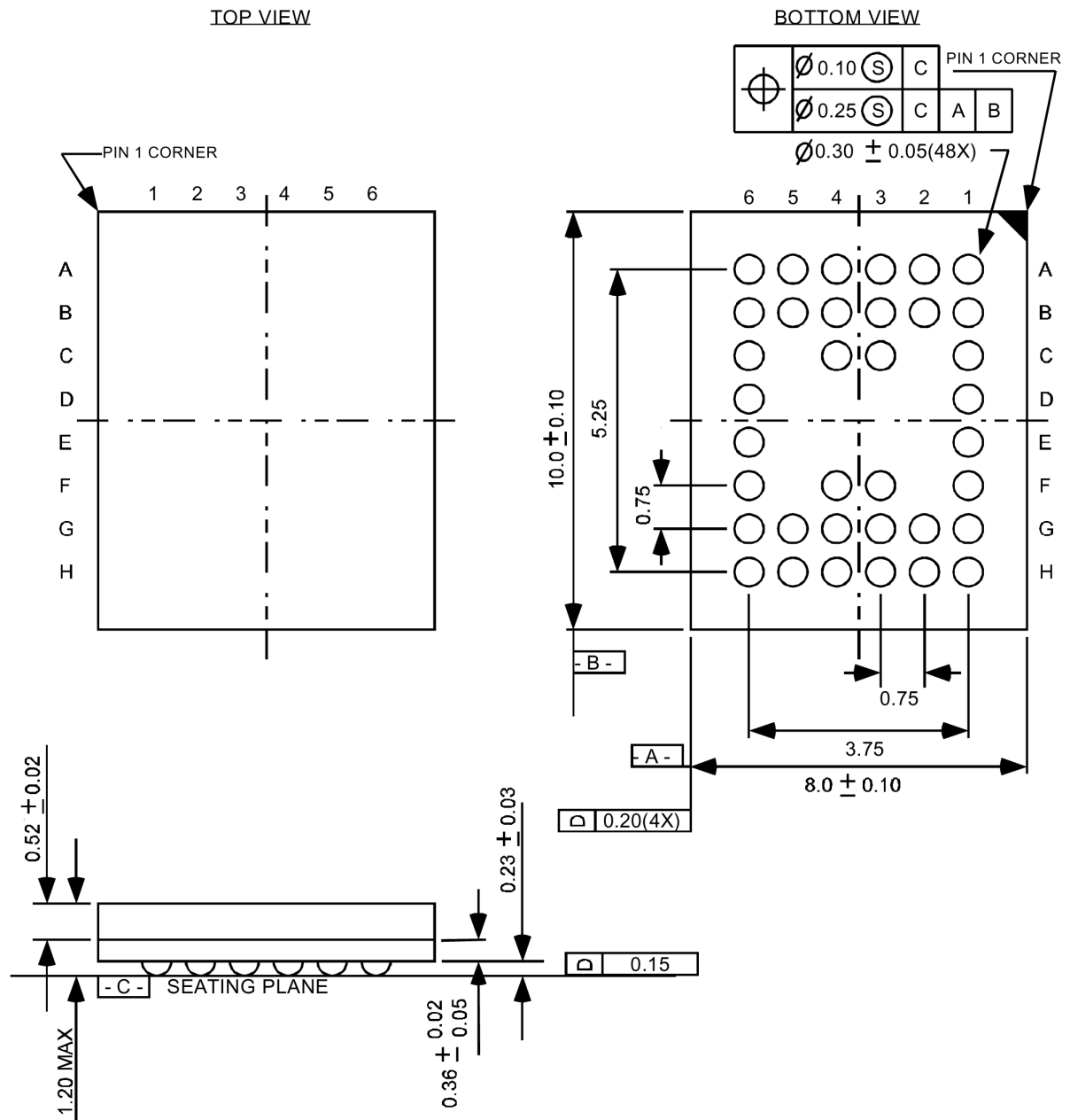


32 pin 8mm x 13.4mm STSOP Package Outline Dimension

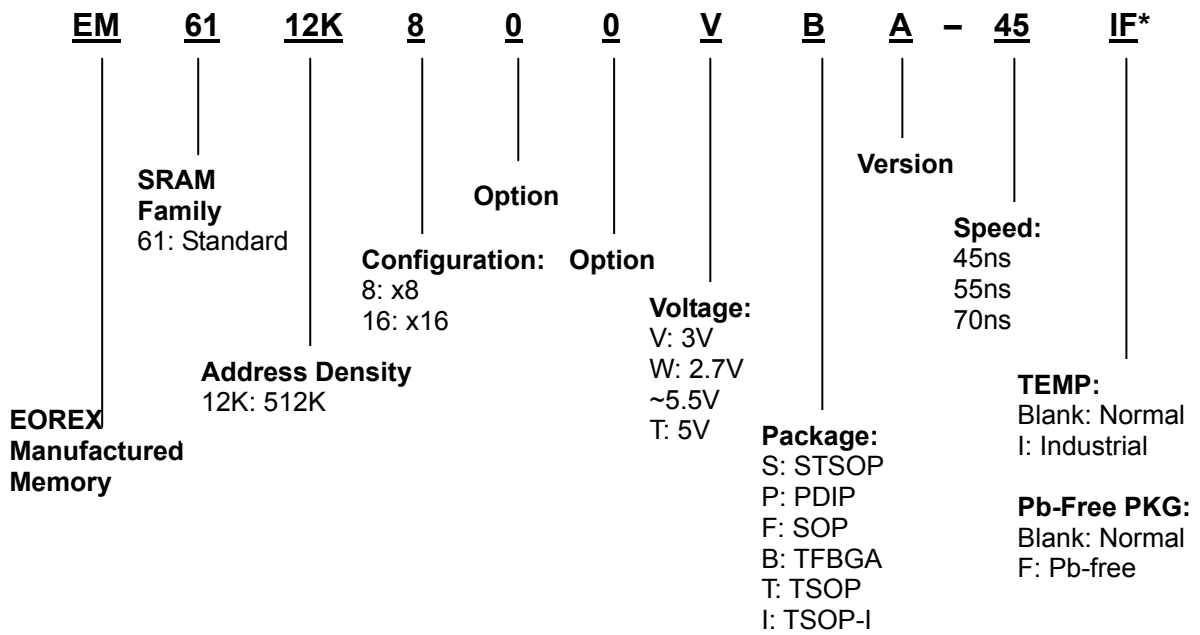


Symbol	Dimension in Inches			Dimension in mm		
	Min.	Nom.	Max.	Min.	Nom.	Max.
A			0.047			1.20
A ₁	0.002		0.006	0.05		0.15
A ₂	0.035	0.040	0.041	0.95	1.00	1.05
b	0.007	0.009	0.010	0.17	0.22	0.27
c	0.004	-----	0.008	0.10	-----	0.21
D		0.488			12.40	
E		0.315			8.00	
H _D		0.551			14.00	
e		0.020			0.50	
L	0.020	0.024	0.028	0.50	0.60	0.70
L ₁		0.031			0.80	
Y	0.000		0.004	0.00		0.10
θ	0	3	5	0	3	5

36-ball 6mm × 8mm TFBGA Package Outline Dimension



Product ID Information



* Product ID example

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